



Is Now Part of



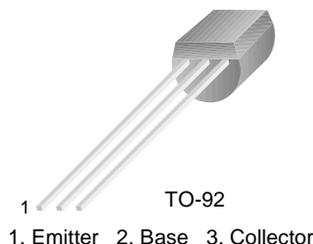
**ON Semiconductor®**

To learn more about ON Semiconductor, please visit our website at  
[www.onsemi.com](http://www.onsemi.com)

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

# KSP92/93

## High Voltage Transistor



## PNP Epitaxial Silicon Transistor

### Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage : KSP92 : KSP93	-300	V
		-200	V
$V_{CEO}$	Collector-Emitter Voltage : KSP92 : KSP93	-300	V
		-200	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-500	mA
$P_C$	Collector Power Dissipation ( $T_a=25^\circ\text{C}$ )	625	mW
	Derate above $25^\circ\text{C}$	5	mW/ $^\circ\text{C}$
$P_C$	Collector Power Dissipation ( $T_C=25^\circ\text{C}$ )	1.5	W
	Derate above $25^\circ\text{C}$	12	mW/ $^\circ\text{C}$
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	-55 ~ 150	$^\circ\text{C}$

### Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage : KSP92 : KSP93	$I_C = -100\mu\text{A}, I_E = 0$	-300		V
			-200		V
$BV_{CEO}$	* Collector-Emitter Breakdown Voltage : KSP92 : KSP93	$I_C = -1\text{mA}, I_B = 0$	-300		V
			-200		V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = -100\mu\text{A}, I_C = 0$	-5		V
$I_{CBO}$	Collector Cur-off Current : KSP92 : KSP93	$V_{CB} = -200\text{V}, I_E = 0$ $V_{CB} = -160\text{V}, I_E = 0$		-0.25	$\mu\text{A}$
				-0.25	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = -3\text{V}, I_C = 0$		-0.10	$\mu\text{A}$
$h_{FE}$	* DC Current Gain	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$ $V_{CE} = -10\text{V}, I_C = -10\text{mA}$ $V_{CE} = -10\text{V}, I_C = -30\text{mA}$	25		
			40		
			25		
$V_{CE}(\text{sat})$	*Collector-Emitter Saturation Voltage	$I_C = -20\text{mA}, I_B = -2\text{mA}$		-0.50	V
$V_{BE}(\text{sat})$	* Base-Emitter Saturation Voltage	$I_C = -20\text{mA}, I_B = -2\text{mA}$		-0.90	V
$f_T$	Current Gain Bandwidth Product	$V_{CE} = -20\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$	50		MHz
$C_{ob}$	Output Capacitance : KSP92 : KSP93	$V_{CB} = -20\text{V}, I_E = 0$ $f = 1\text{MHz}$		6	pF
				8	pF

\* Pulse Test:  $PW \leq 300\mu\text{s}$ , Duty Cycles  $\leq 2\%$

# Typical Characteristics

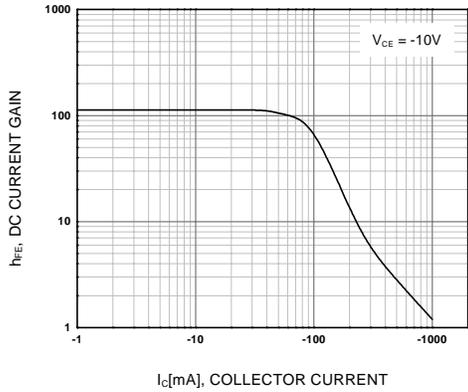


Figure 1. DC current Gain

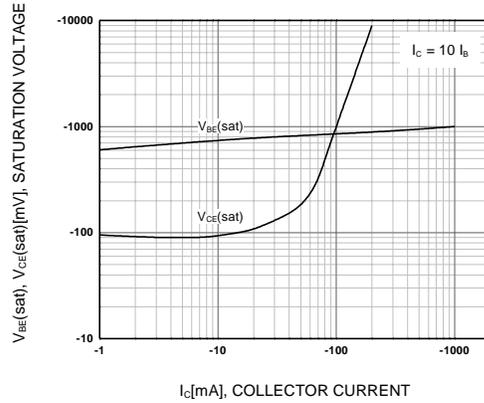


Figure 2. Saturation Voltage

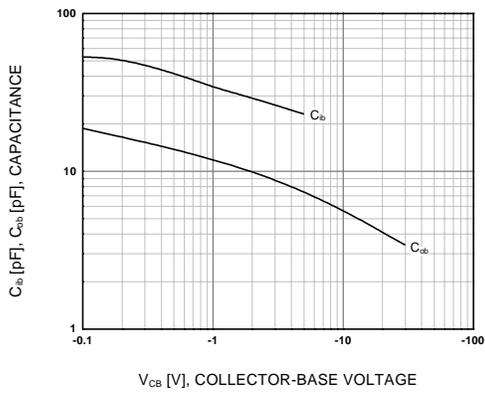


Figure 3. Capacitance

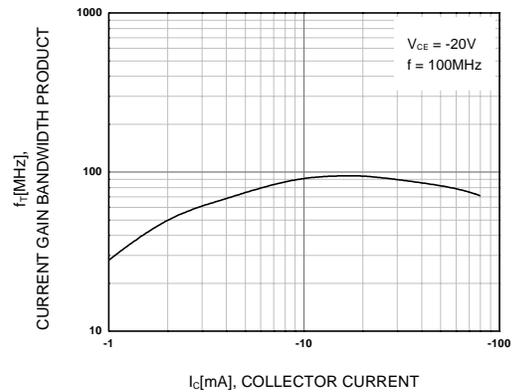


Figure 4. Current Gain Bandwidth Product

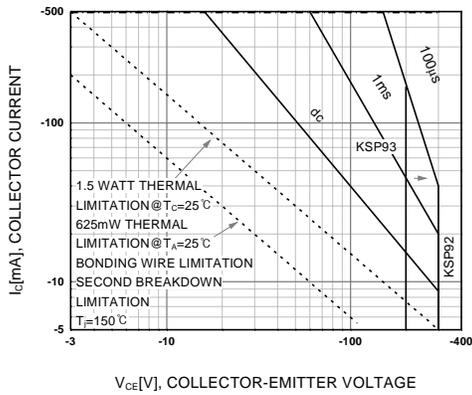
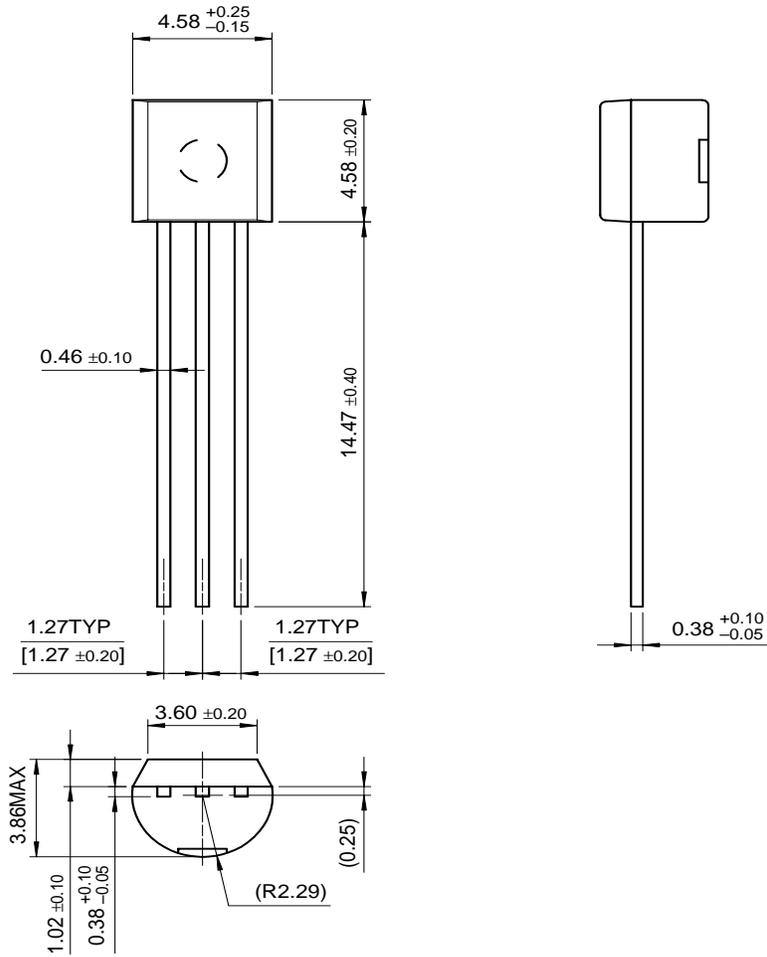


Figure 5. Active-Region Safe Operating Area

# Package Dimensions

KSP92/93

## TO-92



Dimensions in Millimeters